

P-Channel 2.5 V (G-S) MOSFET

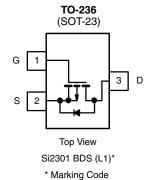
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A) ^b			
- 20	0.100 at V _{GS} = - 4.5 V	- 2.4			
- 20	0.150 at V _{GS} = - 2.5 V	- 2.0			

FEATURES

- Halogen-free According to IEC 61249-2-21
- TrenchFET® Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



HALOGEN FREE



Ordering Information: Si2301BDS-T1-E3 (Lead (Pb)-free)

Si2301BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted)						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V _{DS}	- 20		٧	
Gate-Source Voltage		V _{GS}	± 8			
Continuous Drain Current (T, I = 150 °C) ^b	T _A = 25 °C	I _D	- 2.4	- 2.2		
Continuous Drain Current (1 _J = 150 °C)	T _A = 70 °C		- 1.9	- 1.8		
Pulsed Drain Current ^a		I _{DM}	- 10		Α	
Continuous Source Current (Diode Conduction) ^b		I _S	- 0.72	- 0.6		
Barrar Bitation than h	T _A = 25 °C	P _D	0.9	0.7	W	
Power Dissipation ^b	T _A = 70 °C] 'D	0.57	0.45		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^b	- R _{thJA}	120	145	°C/W	
Maximum Junction-to-Ambient ^c	TithJA	140	175	C/VV	

- a. Pulse width limited by maximum junction temperature.
- b. Surface mounted on FR4 board, $t \le 5$ s.
- c. Surface mounted on FR4 board.

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply.

Si2301BDS

Vishay Siliconix



SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	- 20			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	- 0.45		- 0.95	, v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current	1	V _{DS} = - 20 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 20 V, V _{GS} = 0 V, T _J = 55 °C			- 10	μΑ	
		$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 6			_	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -2.5 \text{ V}$	- 3			A	
	Ъ	$V_{GS} = -4.5 \text{ V}, I_D = -2.8 \text{ A}$		0.080	0.100		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -2 \text{ A}$		0.110	0.150	Ω	
Forward Transconductance ^a	g _{fs}	V _{DS} = - 5 V, I _D = - 2.8 A		6.5		S	
Diode Forward Voltage	V_{SD}	$I_S = -0.75 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.80	- 1.2	V	
Dynamic ^b							
Total Gate Charge	Qg	V - 6VV - 45V		4.5	10		
Gate-Source Charge	Q_{gs}	$V_{DS} = -6 \text{ V}, V_{GS} = -4.5 \text{ V}$ $I_{D} \cong -2.8 \text{ A}$		0.7		nC	
Gate-Drain Charge	Q_{gd}	10 = 2.5 A		1.1		1	
Gate Resistance	R_g	f = 1 MHz	2	8	16	Ω	
Input Capacitance	C _{iss}			375			
Output Capacitance	C _{oss}	$V_{DS} = -6 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		95		pF	
Reverse Transfer Capacitance	C _{rss}			65			
Switching ^c							
Turn-On Time	t _{d(on)}	V 0VP 00		20	30		
ium-on fille	t _r	$V_{DD} = -6 \text{ V}, R_L = 6 \Omega$ $I_D \cong -1 \text{ A}, V_{GEN} = -4.5 \text{ V}$		40	60	ne	
Turn-Off Time	t _{d(off)}	$R_a = 6 \Omega$		30	45	ns	
ium-on time	t _f	g		20	30		

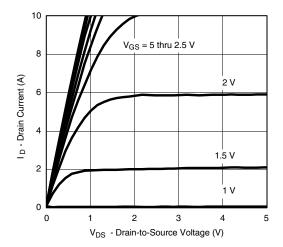
Notes:

- a. Pulse test: pulse width \leq 300 μ s duty cycle \leq 2 %.
- b. For DESIGN AID ONLY, not subject to production testing.
- c. Switching time is essentially independent of operating temperature.

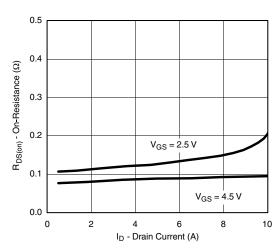
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



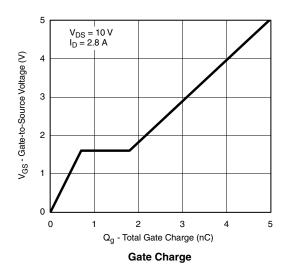
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

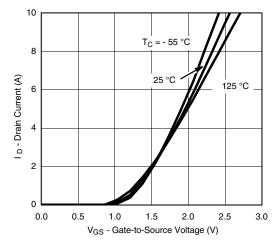


Output Characteristics

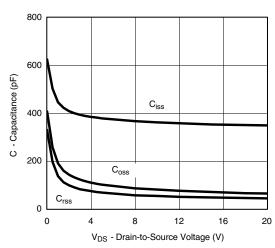


On-Resistance vs. Drain Current

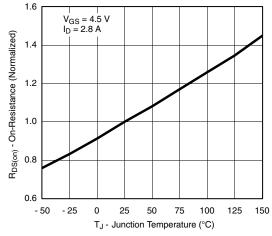




Transfer Characteristics

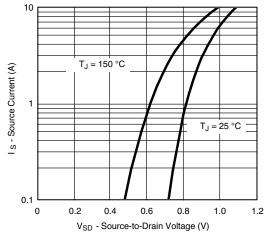


Capacitance

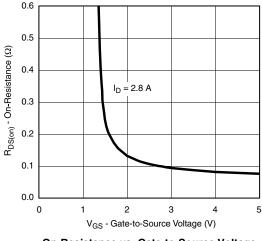


On-Resistance vs. Junction Temperature

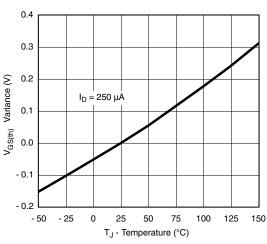
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



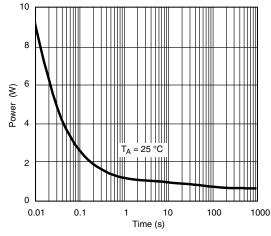
Source-Drain Diode Forward Voltage



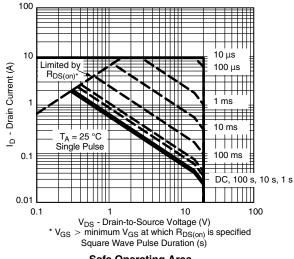
On-Resistance vs. Gate-to-Source Voltage



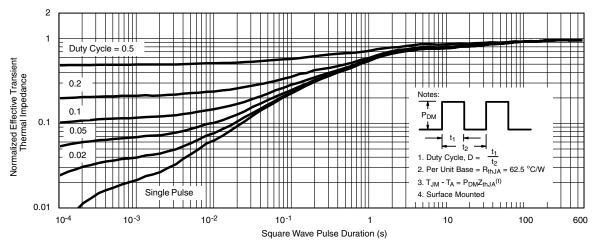
Threshold Voltage



Single Pulse Power



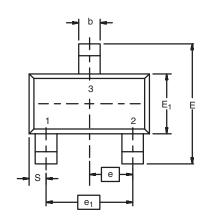
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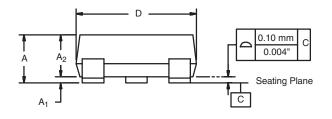


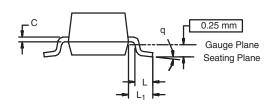
Normalized Thermal Transient Impedance, Junction-to-Ambient

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SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES		
	Min	Max	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
Е	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
FCN: S-03946-Rev K 09-	lul-01				

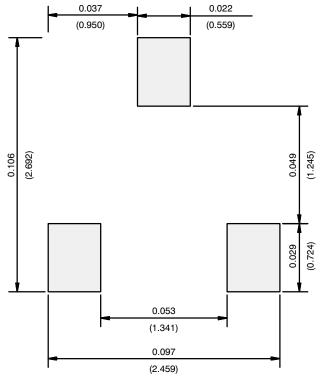
ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

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RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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